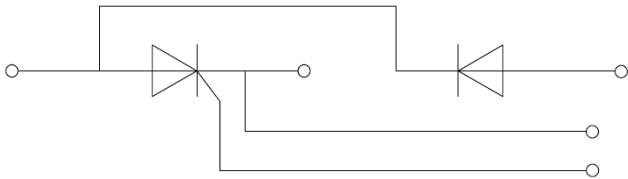




CJ &A (&J

J C

F	L	K
°C		



C H

F		I	L	K
	°C			
				°C
				°C



F		I	L			K
			C	J	C	
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					

J

F		I	L			K
			C	J	C	

E

	C	F	M		F

J

J

FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)

 $P_T(AV)/P_F(AV)(W)$

FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

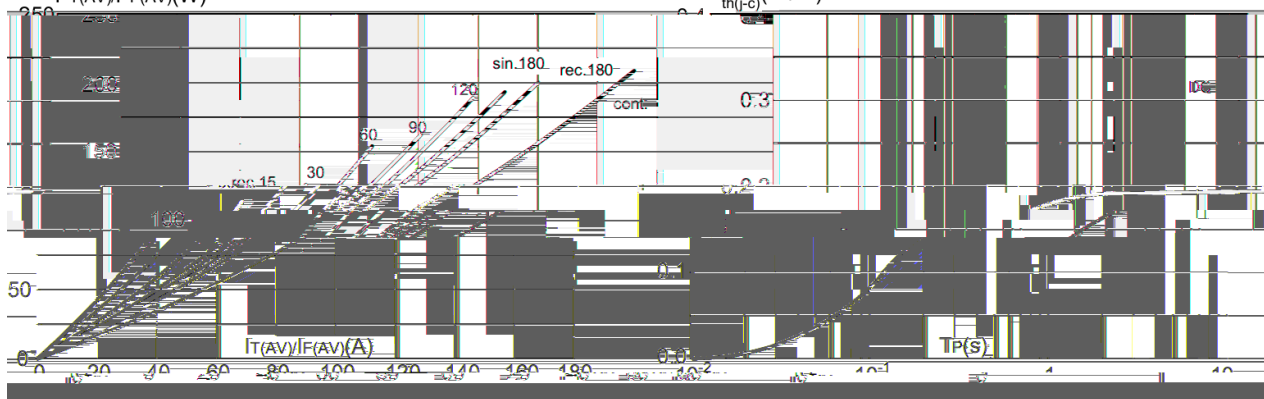
 $R_{th(j-c)}(^{\circ}C/W)$


FIG.3: Forward characteristics

(per thyristor or diode)

FIG.4: Relative variations of gate trigger current, holding

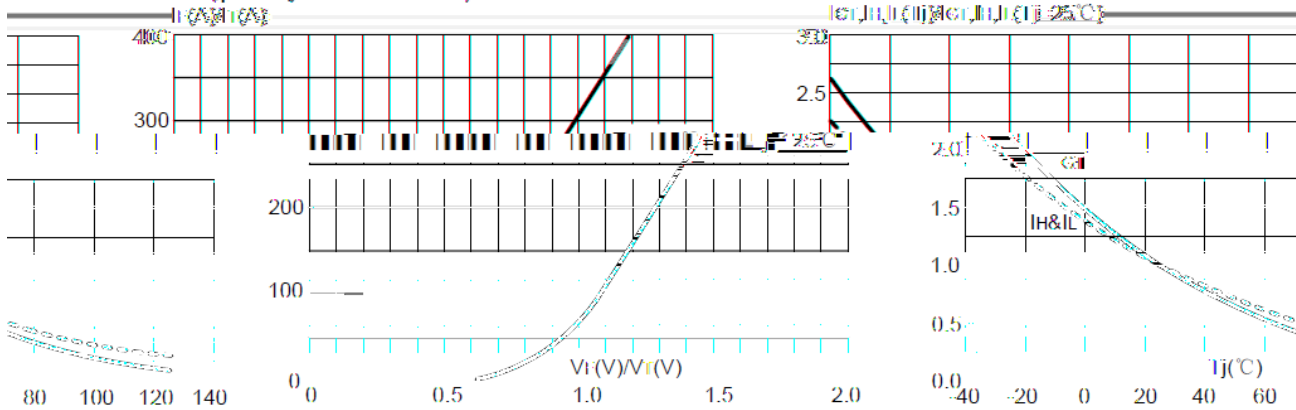
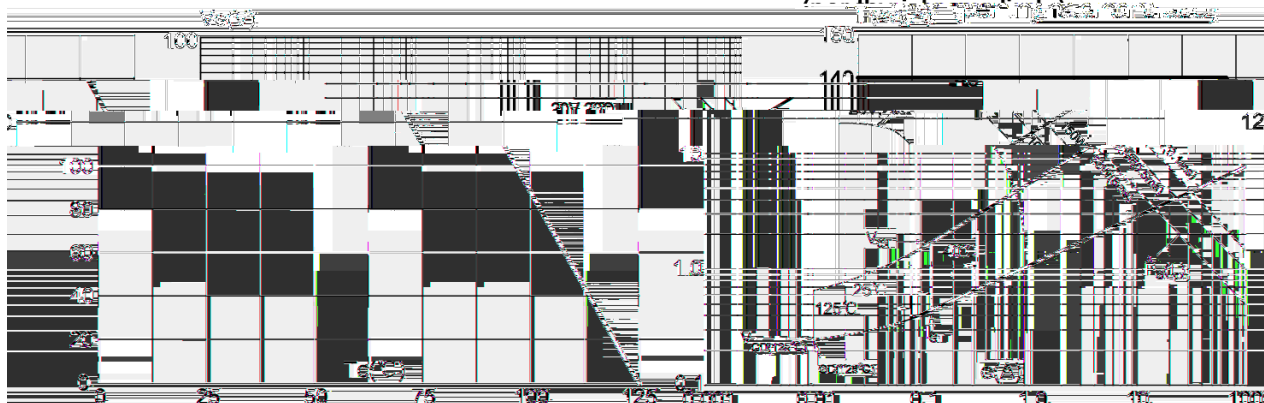
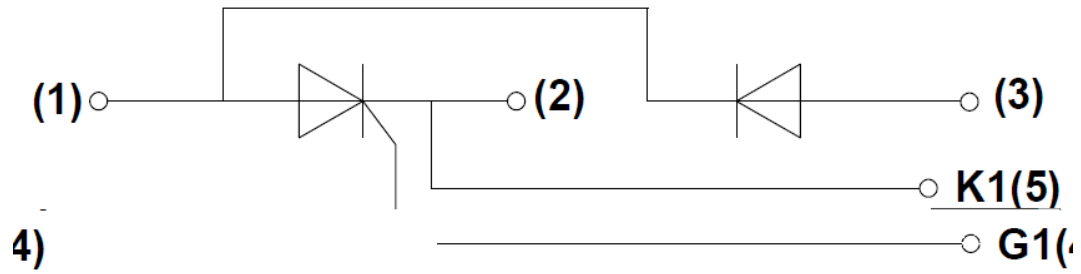
current and latch requirement versus ambient temperature (per H, L, H&L) ($T_J 25^{\circ}C$)


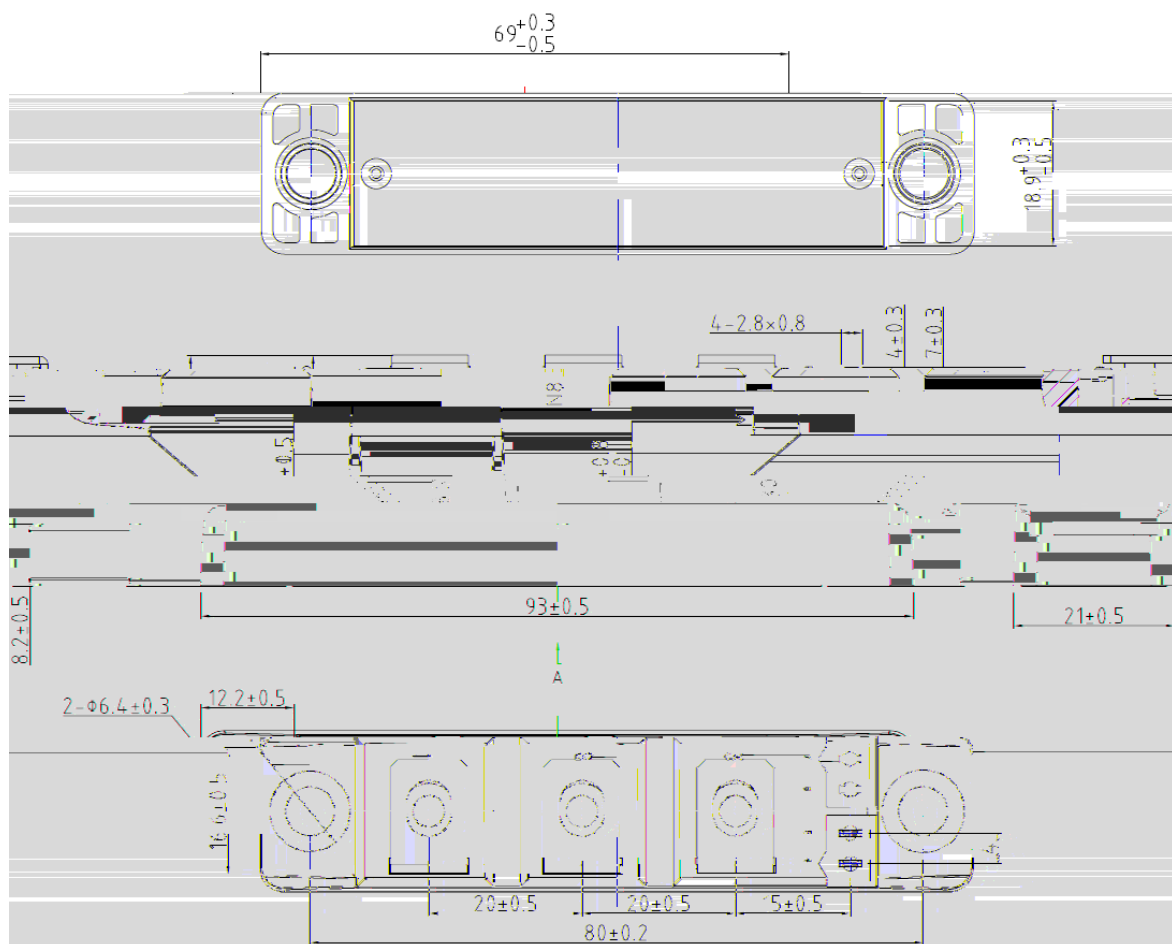
FIG.5 Gate trigger characteristics

FIG.6: Forward current vs. case temperature





F E





CJ &A (&J

